

PRODUCT/PROCESS CHANGE NOTICE (PCN)			
PCN #: W1101-02R2 Product Affected: Refer Attachm  Date Effective: September 13, 20	DATE January 27, 2014 nent II	MEANS OF DISTINGUISHING CHANGED DEVICES:  ■ Product Mark	
Contact: IDT PCN DESK	·	Attachment: Yes No	
E-mail: pcndesk@idt.co	<u>m</u>	Samples: Available upon request	
DESCRIPTION AND PURPOSE	OF CHANGE:		
<ul><li>□ Die Technology</li><li>□ Wafer Fabrication Process</li><li>□ Assembly Process</li></ul>	Die Technology Wafer Fabrication Process Wafer Fabrication Process Wafer Fabrication Process  Revision 2: This revised notification is to provide the new orderable part numbers for device fabricated at TSMC. In addition, several devices are removed from the affected list of part numbers. PCN effective date remains unchanged		
☐ Equipment ☐ Material ☐ Testing	This is to notify our customers that IDT has successfully transferred the wafer fabrication from IDT Hillsboro, Oregon (Fab 4) to Taiwan Semiconductor Manufacturing Corporation (TSMC).		
■ Manufacturing Site	There is no expected change to t	he data sheet, package or backend manufacturing process.	
☐ Data Sheet ☐ Other	IDT Hillsboro, Oregon (Fab 4) is no longer in production and all future wafer fabrication will be at TSMC Fab.		
	Attachment I details the qualific Attachment II details the updated		
<b>RELIABILITY/QUALIFICATIO</b> Based on wafer and component lever reliability of the product.		on tests, there is no change to the performance or	
to grant approval or request additional it will be assumed that this change	ire written notification of this char onal information. If IDT does not a is acceptable. or version manufactured after the p	nge. Please use the acknowledgement below or E-Mail receive acknowledgement within 30 days of this notice process change effective date until the inventory	
Customer:		Approval for shipments prior to effective date.	
Name/Date:	E-	Mail Address:	
Title: Pho		one# /Fax# :	
CUSTOMER COMMENTS:			
IDT ACKNOWLEDGMENT OF	RECEIPT:		
RECD. BY:		DATE:	

## PRODUCT/PROCESS CHANGE NOTICE (PCN)

#### ATTACHMENT I - PCN #: W1101-02R2

**PCN Type:** Wafer Fab Manufacturing Site Change - IDT Fab 4 to TSMC

**Data Sheet Change:** None

**Detail Of Change:** 

Revision 2: This revised notification is to provide the new orderable part numbers for devices fabricated at TSMC. Refer to Table 1. In addition, several devices are removed from the affected list of part numbers. Refer to Attachment II.

This is to notify our customers that IDT has successfully transferred the wafer fabrication from IDT Hillsboro, Oregon (Fab 4) to Taiwan Semiconductor Manufacturing Corporation (TSMC).

There is no expected change to the data sheet, package or backend manufacturing process.

IDT Hillsboro, Oregon (Fab 4) is no longer in production and all future wafer fabrication will be at TSMC Fab.

Table 1

Old Part Number	New Part Number
(IDT Fab 4)	(TSMC Fab)
1337GDVGI	1337AGDVGI
1337GDVGI8	1337AGDVGI8
1337GDCGI	1337AGDCGI
1337GDCGI8	1337AGDCGI8
1337GCSRI	1337AGCSRGI
1337GCSRI8	1337AGCSRGI8
1338-18DCGI	1338-18DCGI
1338-18DVGI	1338-18DVGI
1338-31DCGI	1338-31DCGI
1338-31DVGI	1338-31DVGI
1338-18DCGI8	1338-18DCGI8
1338-18DVGI8	1338-18DVGI8
1338-31DCGI8	1338-31DCGI8
1338-31DVGI8	1338-31DVGI8
1338C-18SRI	1338C-18SRGI
1338C-31SRI	1338C-31SRGI
1338C-18SRI8	1338C-18SRGI8
1338C-31SRI8	1338C-31SRGI8
1339-2DCGI	1339-2DCGI
1339-2DVGI	1339-2DVGI
1339-31DCGI	1339-31DCGI
1339-31DVGI	1339-31DVGI
1339C-2SRI	1339C-2SRGI
1339C-31SRI	1339C-31SRGI
1339-2DCGI8	1339-2DCGI8
1339-2DVGI8	1339-2DVGI8
1339-31DCGI8	1339-31DCGI8
1339-31DVGI8	1339-31DVGI8
1339C-2SRI8	1339C-2SRGI8
1339C-31SRI8	1339C-31SRGI8
5P90005CDCGI	5P90005CDCGI
5P90005CDCGI8	5P90005CDCGI8

# PRODUCT/PROCESS CHANGE NOTICE (PCN)

#### ATTACHMENT I - PCN #: W1101-02R2

#### **Qual Plan & Results:**

#### TSMC Transfer Qualification Test Result Summary

Technology Information: 0.18 μm Fab Location: TSMC Fab 8

#### Technology Qualification Vehicle Test Summary - JESD47 Recommended Tests

Test / Conditions	Lead Vehicle: 6V40107 (AT294)
	Sample Size / Rejects/ each lot
High Temperature Operating Life (Dynamic) JESD22-A108B, +125°C @ 1000 hours or equivalent	77 / 0 77 / 0 77 / 0
Temperature Cycle JESD22-A104B, -55°C -/125°C, 1000 cycles	25/0 25/0 25/0 25/0
High Temperature Storage Bake JESD22-A-103-B, 150°C, 1000 hrs	25 / 0 25 / 0 25 / 0
ESD: Human Body Model JESD22-A114F , >2000V	3 / 0
ESD: Charged Device Model JEDEC 22-101C; >500V	3 / 0
Latch-up JESD78B	6 / 0
Electrical Characterization per Datasheet conditions	Pass

#### Technology Qualification Vehicle Test Summary - Supplemental Tests

Test / Conditions	Lead Vehicle: : 6V40107 (AT294) Sample Size / Rejects/ each lot
Ball Shear Test JESD22-B116-A, Ball Shear Strength > 5.7g	5 / 0 5 / 0 5 / 0
Highly Accelerated Stress Test (HAST) EIA/ÆSD22-Al 10B, 130°C/85%R.H. Vcc max for 100 hours.	25/0 25/0 25/0
Autoclave EIA/JESD22-Al02C, 168hrs @ 2 ATM, Saturated Steam @ 121°C	25/0 25/0 25/0

Note: For HAST, Autoclave and Temperature Cycle, samples have been subjected to pre-conditioning per JESD22-Al 13

# PRODUCT/PROCESS CHANGE NOTICE (PCN)

#### ATTACHMENT I - PCN #: W1101-02R2

#### **Qual Plan & Results:**

#### TSMC Transfer Qualification Test Result Summary

Technology Information: 0.18 μm, 3.3 V Fab Location: TSMC Fab 8

#### Technology Qualification Vehicle Test Summary - JESD47 Recommended Tests

Test / Conditions	Lead Vehicle: 9LPRS387 (AP298)
	Sample Size / Rejects/ each lot
High Temperature Operating Life (Dynamic) JESD22-A108B, +125°C @ 1000 hours or equivalent	77/0 77/0 77/0
Temperature Cycle JESD22-A104B, -55°C -/125°C, 1000 cycles	45 / 0 45 / 0 45 / 0
High Temperature Storage Bake JESD22-A-103-B, 150°C, 1000 hrs	77 / 0 77 / 0 77 / 0
ESD: Human Body Model JESD22-A114F	5 / 0
ESD: Charged Device Model JEDEC 22-101C	5 / 0
ESD: Machine Model JESD22-Al 15B	5 / 0
Latch-up JESD78B	6 / 0
Electrical Characterization per Datasheet conditions	10

#### Technology Qualification Vehicle Test Summary - Supplemental Tests

Test / Conditions	Lead Vehicle: 9LPRS387 (AP298) Sample Size / Rejects/ each lot
Ball Shear Test JESD22-B116-A, Ball Shear Strength > 5.7g	5 / 0 5 / 0 5 / 0
Highly Accelerated Stress Test (HAST) EIA/JESD22-Al 10B, 130°C/85%R.H. Vcc max for 100 hours.	45 / 0 45 / 0 45 / 0
Autoclave EIA/JESD22-Al02C, 168hrs @ 2 ATM, Saturated Steam @ 121°C	45/0 45/0 45/0

Note: For HAST, Autoclave and Temperature Cycle, samples have been subjected to pre-conditioning per JESD22-All3

# PRODUCT/PROCESS CHANGE NOTICE (PCN)

## ATTACHMENT II - PCN #: W1101-02R2

## **Updated Affected Part Number**

Part Number	Part Number	Part Number	Part Number
1337GDVGI	1338-31DCGI	1338C-18SRI8	1339-2DCGI8
1337GDVGI8	1338-31DVGI	1338C-31SRI8	1339-2DVGI8
1337GDCGI	1338-18DCGI8	1339-2DCGI	1339-31DCGI8
1337GDCGI8	1338-18DVGI8	1339-2DVGI	1339-31DVGI8
1337GCSRI	1338-31DCGI8	1339-31DCGI	1339C-2SRI8
1337GCSRI8	1338-31DVGI8	1339-31DVGI	1339C-31SRI8
1338-18DCGI	1338C-18SRI	1339C-2SRI	5P90005CDCGI
1338-18DVGI	1338C-31SRI	1339C-31SRI	5P90005CDCGI8

## Affected Part Number Removed from PCN Revision 2

Part Number	Part Number	Part Number	Part Number
1337ACSRI	1338A-31DVGI8	1339A-31DVGI	1339AC-31SRI8
1337ACSRI8	1338AC-31SRI	1339A-31DVGI8	1337GNLGI
1338A-31DVGI	1338AC-31SRI8	1339AC-31SRI	1337GNLGI8